SOT23-6 P MOS

-CHANNEL MOSFET in a SOT23-6 Plastic Package.

V_{DS} (V) = -16V I_D = -7.0A

$R_{DS(ON)}$@-4.5V(Typ.)=16.7mΩ

$R_{DS(ON)}$@-2.5V(Typ.)=22.5mΩ

$R_{DS(ON)}$@-1.8V(Typ.)=32.5mΩ

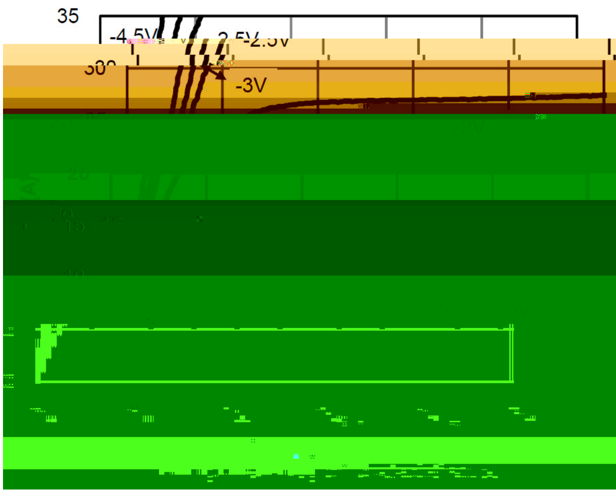
HF Product.

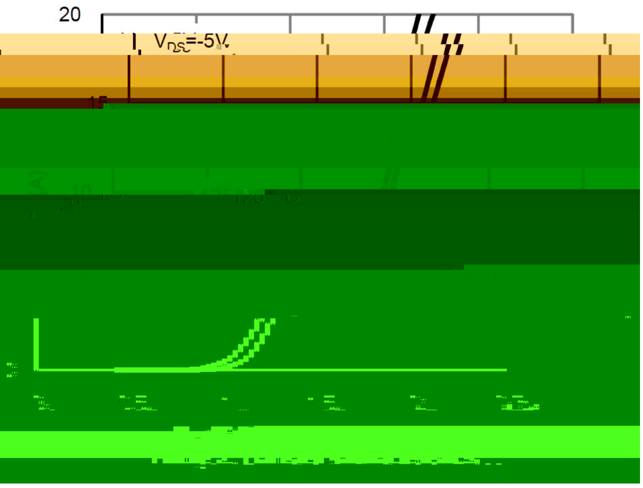
Power Management in Notebook computer, Portable Equipment and Battery powered systems.

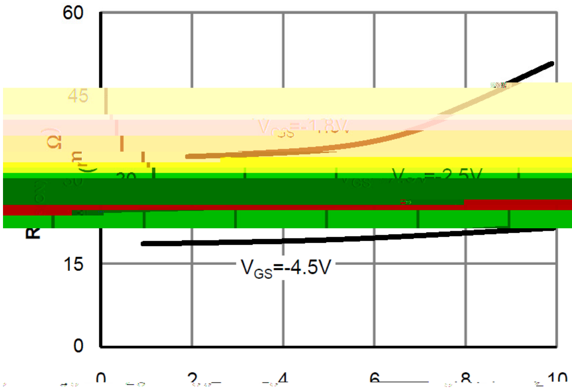
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-16	V
Gate-Source Voltage	V_{GSS}	±12	V
Continuous Drain Current	I_D	-7.0	A
Pulsed Drain Current	I_{DM}	-30	A
Power Dissipation for Single Operation	P_D	1.2	W
Maximum Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	100	/W

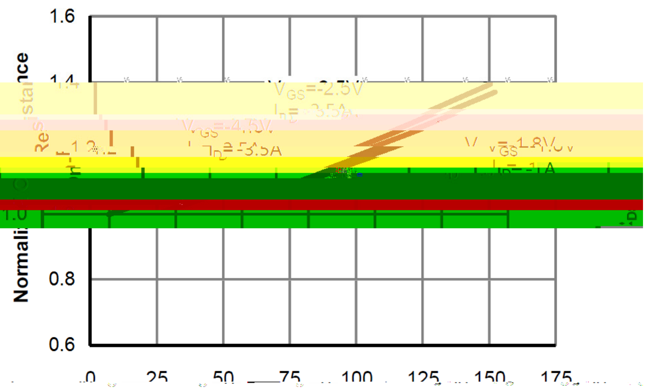
Parameter Symbol

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	Q_g	V_{GS}=-4.5V, V_{DS}=-10V, I_D=-7.0A		13.2		nC
Gate Source Charge	Q_{gs}			1.5		
Gate Drain Charge	Q_{gd}			3.6		
Turn–On Delay Time	$t_{d(on)}$	V_{GS}=-4.5V I_D=-7.0A V_{DS}=-10V R_{GEN}=3Ω		13.7		ns
Turn–On Rise Time	t_r			47.6		
Turn–Off Delay Time	$t_{d(off)}$			43.1		
Turn–Off Fall Time	t_f			29.5		







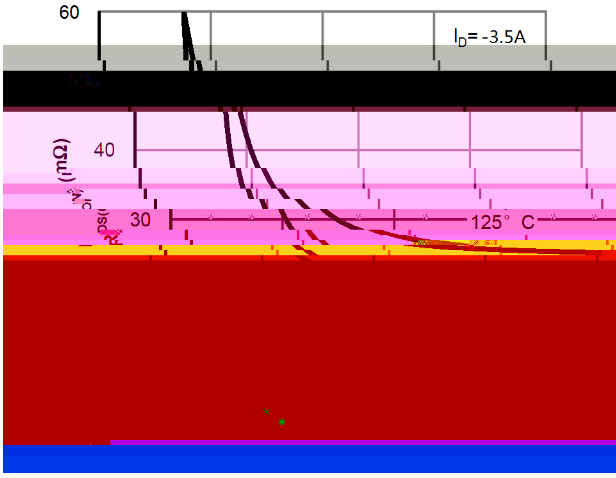


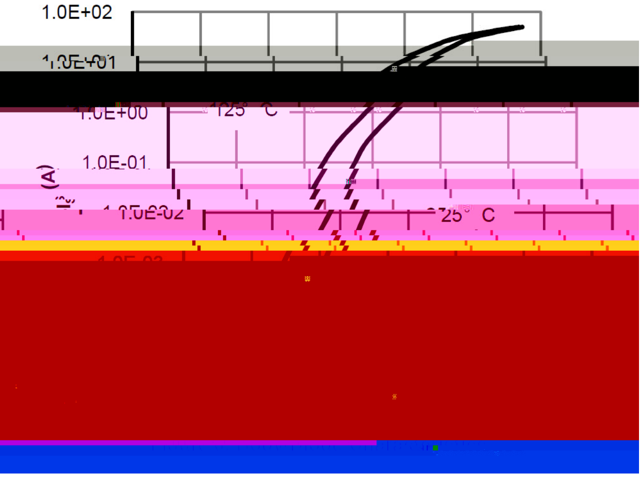
perature (℃)

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Temp

igure 4: On-Resistance vs. Junction Temperature





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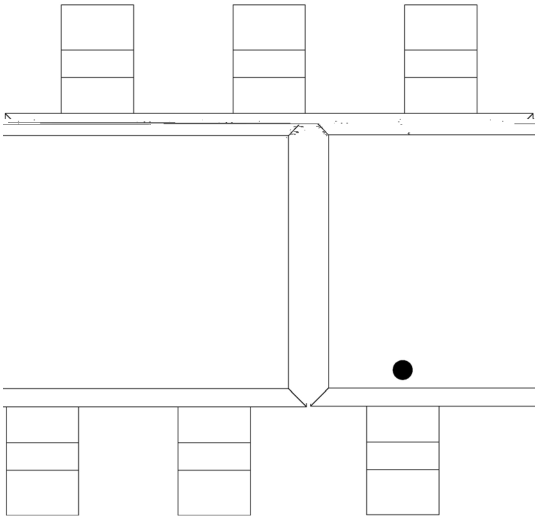

C6

H

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Note:

C6: Product Type Code

H: Company Code